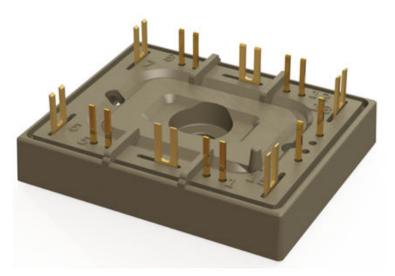
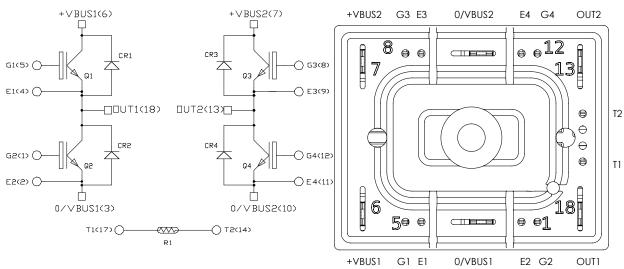
# MSCGLQ50H120CTBL2NG

## Full Bridge High-Speed IGBT4 Power Module

### **Product Overview**

The MSCGLQ50H120CTBL2NG device is a 1200 V/50 A full bridge high-speed IGBT4 power module.





All ratings at  $T_J$  = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are the key features of MSCGLQ50H120CTBL2NG device:

- · High speed IGBT4
  - Low voltage drop
  - Low leakage current
  - Low switching losses
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on V<sub>F</sub>
- Very low stray inductance
- Ultra-low weight and profile
- Kelvin emitter for easy drive
- Si<sub>3</sub>N<sub>4</sub> substrate with thick copper for improved thermal performance
- Internal thermistor for temperature monitoring
- Extended temperature range

#### **Benefits**

The following are the benefits of MSCGLQ50H120CTBL2NG device:

- High efficiency converter
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-heatsink thermal resistance
- Low profile
- RoHS compliant
- Solderable terminals both for power and signal for easy PCB mounting
- Very integrated power conversion system

## **Application**

The following are the applications of MSCGLQ50H120CTBL2NG device:

- High reliability power systems
- High efficiency AC/DC and DC/AC converters
- Motor control

DS00004104A-page 2 **Datasheet** 

## 1. Electrical Specifications

This section provides the electrical specifications of MSCGLQ50H120CTBL2NG device.

## 1.1 IGBT4 Characteristics (Per IGBT)

The following table lists the absolute maximum ratings of MSCGLQ50H120CTBL2NG device.

**Table 1-1. Absolute Maximum Ratings** 

Symbol	Parameter	Parameter		
V <sub>CES</sub>	Collector-Emitter voltage	Collector-Emitter voltage		V
I <sub>C</sub>	Continuous collector current	T <sub>H</sub> = 25 °C	110	А
		T <sub>H</sub> = 100 °C	50	
I <sub>CM</sub>	Pulsed collector current	T <sub>H</sub> = 25 °C	180	
V <sub>GE</sub>	Gate-Emitter voltage	Gate-Emitter voltage		V
$P_{D}$	Power dissipation	T <sub>H</sub> = 25 °C	375	W

The following table lists the electrical characteristics of MSCGLQ50H120CTBL2NG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>CES</sub>	Zero gate voltage collector current	V <sub>GE</sub> = 0 V V <sub>CE</sub> = 1200 V		_	_	25	μΑ
V <sub>CE(sat)</sub>	Collector emitter	V <sub>GE</sub> = 15 V	T <sub>J</sub> = 25 °C	1.7	2.05	2.4	V
	saturation voltage	I <sub>C</sub> = 50 A	T <sub>J</sub> = 150 °C	_	2.6	_	
$V_{GE(th)}$	Gate threshold voltage	$V_{GE} = V_{CE}$ $I_C = 1.7 \text{ mA}$		5.3	5.8	6.3	V
I <sub>GES</sub>	Gate-Emitter leakage current	V <sub>GE</sub> = 20 V V <sub>CE</sub> = 0 V		_	_	150	nA

The following table lists the dynamic characteristics of MSCGLQ50H120CTBL2NG device.

#### **Table 1-3. Dynamic Characteristics**

Symbol	Characteristic	Test Condition	ons		Min	Тур	Max	Unit
C <sub>ies</sub>	Input capacitance	V <sub>GE</sub> = 0 V			_	2770	_	pF
C <sub>oes</sub>	Output capacitance	V <sub>CE</sub> = 25 V			_	185	_	
C <sub>res</sub>	Reverse transfer capacitance	f = 1 MHz			_	160	_	
Q <sub>g</sub>	Total gate charge	V <sub>GE</sub> = 15 V V <sub>CE</sub> = 960 V I <sub>C</sub> = 50 A			_	230	_	nC
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GE</sub> = ±15 V		T <sub>J</sub> = 150 °C	_	30	_	ns
T <sub>r</sub>	Rise time	V <sub>Bus</sub> = 600 V			_	49	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>C</sub> = 50 A			_	366	_	
T <sub>f</sub>	Fall time	$R_G = 10 \Omega$	$R_{G} = 10 \Omega$			48	_	
E <sub>on</sub>	Turn-on switching energy	$V_{GE} = \pm 15 \text{ V}$ $V_{Bus} = 600 \text{ V}$		T <sub>J</sub> = 150 °C	_	2.8	_	mJ
E <sub>off</sub>	Turn-off switching energy	$I_C = 50 \text{ A}$ $R_G = 10 \Omega$		T <sub>J</sub> = 150 °C	_	2.8	_	
$R_G$	Integrated gate resiste	or			_	4	_	Ω
I <sub>SC</sub>	Short circuit data		$V_{GE} \le 15 \text{ V}$ $V_{Bus} = 900 \text{ V}$ $t_p \le 10  \mu \text{s}$	T <sub>j</sub> = 150 °C	_	190		A
R <sub>thJH</sub>	Junction-to-heatsink thermal resistance		$\lambda_{\text{paste}} = 3.4 \text{ W/r}$	nK		0.4	_	°C/W

### 1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of MSCGLQ50H120CTBL2NG device.

Table 1-4. Chopper SiC Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
V <sub>RRM</sub>	Peak repetitive reverse vo	oltage			_	<u> </u>	1200	V
I <sub>RM</sub>	Reverse leakage current	nt V <sub>R</sub> = 1200 V		T <sub>J</sub> = 25 °C	_	10	200	μΑ
				T <sub>J</sub> = 175 °C	_	150	_	
I <sub>F</sub>	DC forward current			T <sub>H</sub> = 100 °C	_	30	_	Α
V <sub>F</sub>	Diode forward voltage	e I <sub>F</sub> = 30 A		T <sub>J</sub> = 25 °C	_	1.5	1.8	V
				T <sub>J</sub> = 175 °C	_	2.1	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 600 V			_	130		nC
С	Total capacitance	f = 1 MHz V <sub>R</sub> = 400 V f = 1 MHz V <sub>R</sub> = 800 V		_	141	_	pF	
					_	105	_	
R <sub>thJH</sub>	Junction-to-heatsink therr resistance	mal $\lambda_{paste} = 3$ .		4 W/mK	_	0.854	_	°C/W

## 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of MSCGLQ50H120CTBL2NG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
V <sub>ISOL</sub>	RMS isolation voltage, any termin 50 Hz/60 Hz	2500	_	_	V		
$T_{J}$	Operating junction temperature r	Operating junction temperature range				175	°C
T <sub>JOP</sub>	Recommended junction tempera conditions	<b>–</b> 55	_	T <sub>Jmax</sub> –25			
T <sub>STG</sub>	Storage case temperature	Storage case temperature			_	125	
T <sub>C</sub>	Operating case temperature			<b>-</b> 55	_	125	
Torque	Mounting torque To heatsink M4		1.5	_	2	N.m	
Wt	Package weight			_	21.5	_	g

The following table lists the temperature sensor NTC of MSCGLQ50H120CTBL2NG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic			Тур	Max	Unit
R <sub>25</sub>	Resistance at 25 °C		_	50	_	kΩ
$\Delta R_{25}/R_{25}$	_			5	_	%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		_	3952	_	K
ΔΒ/Β	_	T <sub>C</sub> = 100 °C	_	4	_	%

$$R_{T} = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

## 1.4 Typical IGBT4 Performance Curve (Per IGBT)

This section shows the typical IGBT4 performance curves of MSCGLQ50H120CTBL2NG device.

Figure 1-1. Junction-to-Heatsink Thermal Impedance

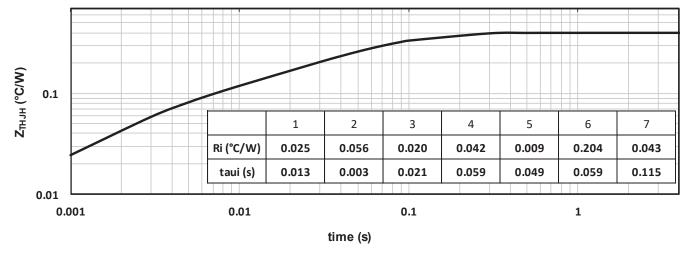


Figure 1-2. Output Characteristics (V<sub>GE</sub> = 15 V)

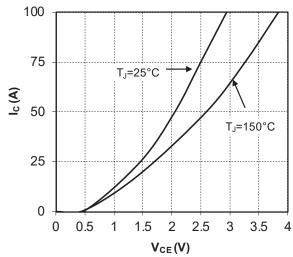


Figure 1-3. Output Characteristics

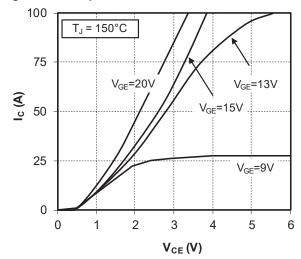


Figure 1-4. Transfer Characteristics

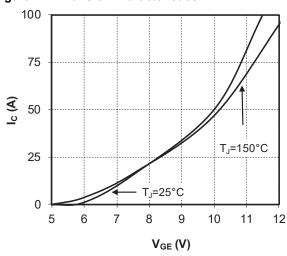


Figure 1-5. Energy losses vs. Collector Current

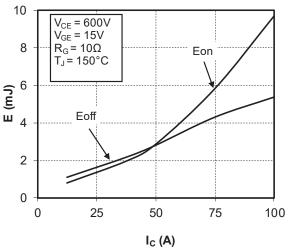


Figure 1-6. Switching Energy Losses vs. Gate Resistance

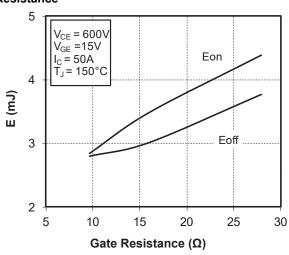
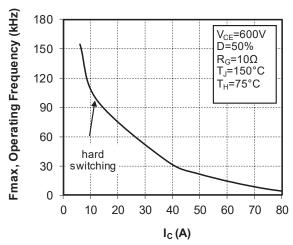


Figure 1-7. Operating Frequency vs. Collector Current



## 1.5 Typical SiC Diode Performance Curve (Per SiC Diode)

This section shows the typical SiC diode performance curves of MSCGLQ50H120CTBL2NG device.

Figure 1-8. Junction-to-Heatsink Thermal Impedance

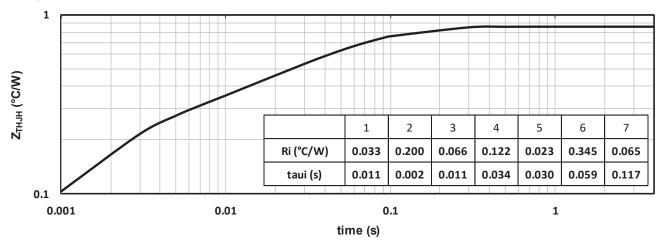


Figure 1-9. Forward Characteristics

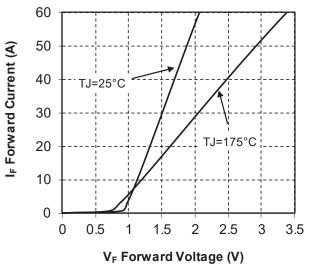
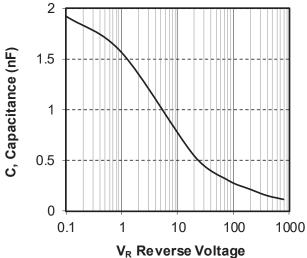


Figure 1-10. Capacitance vs. Reverse Voltage



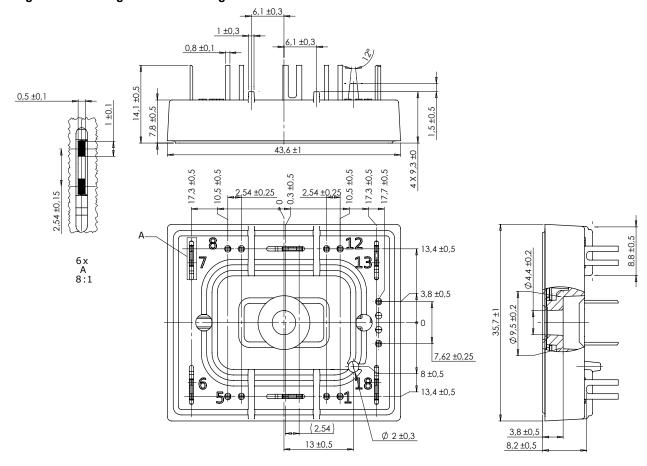
## 2. Package Specifications

The following section shows the package specification of MSCGLQ50H120CTBL2NG device.

## 2.1 Package Outline

The following figure shows the package outline drawing of MSCGLQ50H120CTBL2NG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



## MSCGLQ50H120CTBL2NG

**Revision History** 

## 3. Revision History

Revision	Date	Description
A	07/2021	Initial revision

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